

GB00/3249

PRIORITY DOCUMENT

SUBMITTED OR TRANSMITTED IN
COMPLIANCE WITH RULE 17.1(a) OR (b)

The Patent Office
Concept House
Cardiff Road
Newport
South Wales
NP10 8QQ

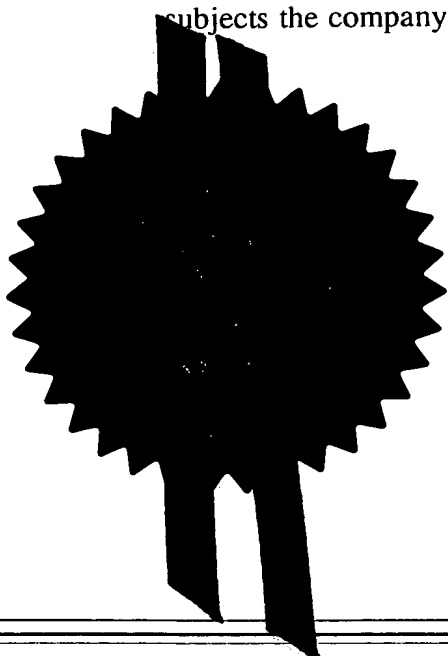
4

I, the undersigned, being an officer duly authorised in accordance with Section 74(1) and (4) of the Deregulation & Contracting Out Act 1994, to sign and issue certificates on behalf of the Comptroller-General, hereby certify that annexed hereto is a true copy of the documents as originally filed in connection with the patent application identified therein.

In accordance with the Patents (Companies Re-registration) Rules 1982, if a company named in this certificate and any accompanying documents has re-registered under the Companies Act 1980 with the same name as that with which it was registered immediately before re-registration save for the substitution as, or inclusion as, the last part of the name of the words "public limited company" or their equivalents in Welsh, references to the name of the company in this certificate and any accompanying documents shall be treated as references to the name with which it is so re-registered.

In accordance with the rules, the words "public limited company" may be replaced by p.l.c., plc, P.L.C. or PLC.

Re-registration under the Companies Act does not constitute a new legal entity but merely subjects the company to certain additional company law rules.



Signed

P. Mahoney

Dated 31 August 2000

1000



1/77

Request for grant of a patent

(See the notes on the back of this form. You can also get an explanatory leaflet from the Patent Office to help you fill in this form)

The Patent Office

Cardiff Road
Newport
Gwent NP9 1RH

1. Your reference

IPD/P2857

2. Patent application number

(The Patent Office will fill in this part)

9921639.2

3. Full name, address and postcode of the or of each applicant (underline all surnames)

The Secretary of State for Defence
Defence Evaluation and Research Agency
Ively Road, Farnborough, Hants, GU14 0LX

Patents ADP number (if you know it)

07710346001

If the applicant is a corporate body, give the country/state of its incorporation

United Kingdom

4. Title of the invention

New Organotellurium Compound and New Method for Synthesising Organotellurium Compounds

5. Name of your agent (if you have one)

A O Bowdery et al

"Address for service" in the United Kingdom to which all correspondence should be sent (including the postcode)

Defence Evaluation & Research Agency
IPD(DERA)Formalities
A4 Bldg
Ively Road,
Farnborough, Hants GU14 0LX, UK

THE PATENT OFFICE

L

15 SEP 1999

RECEIVED BY POST

06812069004

6. If you are declaring priority from one or more earlier patent applications, give the country and the date of filing of the or of each of these earlier applications and (if you know it) the or each application number

Country

Priority application number
(if you know it)

Date of filing
(day / month / year)

7. If this application is divided or otherwise derived from an earlier UK application, give the number and the filing date of the earlier application

Number or earlier application

Date of filing
(day / month / year)

8. Is a statement of inventorship and of right to grant of a patent required in support of this request? (Answer 'Yes' if:

YES

- a) any applicant named in part 3 is not an inventor, or
- b) there is an inventor who is not named as an applicant, or
- c) any named applicant is a corporate body.

Patents Form 1/77

9. Enter the number of sheets for any of the following items you are filing with this form.
Do not count copies of the same document

Continuation sheets of this form

Description

12


Claim(s)

3

Abstract

1

Drawing(s)

3 + 3 

10. If you are also filing any of the following, state how many against each item.

Priority documents

Translations of priority documents

Statement of inventorship and right to grant of a patent (Patents Form 7/77)

1

Request for preliminary examination and search (Patents Form 9/77)

1

Request for substantive examination (Patents Form 10/77)

Any other documents (please specify)

11.

I / We request the grant of a patent on the basis of this application.

Signature



Date

14. 9. 99

12. Name and daytime telephone number of person to contact in the United Kingdom

JB Edwards 01684 89 4002

Warning

After an application for a patent has been filed, the Comptroller of the Patent Office will consider whether publication or communication of the invention should be prohibited or restricted under Section 22 of the Patents Act 1977. You will be informed if it is necessary to prohibit or restrict your invention in this way. Furthermore, if you live in the United Kingdom, Section 23 of the Patents Act 1977 stops you from applying for a patent abroad without first getting written permission from the Patent Office unless an application has been filed at least 6 weeks beforehand in the United Kingdom for a patent of the same invention and either no direction prohibiting publication or communication has been given, or any such direction has been revoked.

Notes

a) If you need help to fill in this form or have any questions, please contact the Patent Office on 0645 500505.

b) Write your answers in capital letters using black ink or you may type them.

c) If there is not enough space for all the relevant details on any part of this form, please continue on a separate sheet of paper and write "see continuation sheet" in the relevant part(s). Any continuation sheet should be attached to this form.

d) If you have attached 'Yes' Patents Form 7/77 will need to be filed.

e) Once you have filled in the form you must remember to sign and date it.

f) For details of the fee and ways to pay please contact the Patent Office.

New Organotellurium Compound and New Method for Synthesising
Organotellurium Compounds

The invention relates to a new organotellurium compound and to new methods of
5 synthesising organoselenium and organotellurium compounds including the new
organotellurium compound. The invention also relates to new electronic devices
and to methods of fabricating such devices.

Cadmium mercury telluride (CMT), mercury telluride (MT), and cadmium telluride
10 (CT) are used in a number of electronic devices including infrared detectors.

Cadmium telluride is also used in solar cells. These materials have the general
formula: $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ where $0 \leq x \leq 1$. If $x=1$ then the material is cadmium telluride, if
 $x=0$ then the material is mercury telluride, if $0 < x < 1$ then the material is cadmium
mercury telluride.

15 These telluride materials are commonly grown by metal organic vapour phase
epitaxy (MOVPE) from organotellurium precursors. In the case of CMT an
organocadmium compound, typically dimethylcadmium, and an organotellurium
compound are heated with mercury in the vapour phase. The arrangement and
20 conditions are such that the organometallic compounds react with each other,
decompose, and react with the mercury resulting in deposition of CMT on a
substrate.

The choice of the organotelluride used is critical to the production of these
25 materials and devices.

There are a large number of organotellurium compounds that might be of value in
deposition of CT/CMT/MT by MOVPE. One variant is that the organo groups could
include alkyl, alkenyl, or aryl groups. Another variant is that compounds having
30 organo groups in the range C_1 to C_6 are all potential candidates as precursors. Yet
another variant is the fact that the telluride may be symmetric or unsymmetric.

Structural isomers add a final multiplier to the number of possible compounds that are candidates as MOVPE precursors.

A number of factors affect the suitability of an organotelluride as an MOVPE precursor.

The decomposition temperature of the organotelluride should be sufficiently low that the CMT, MT, and CT materials can be grown efficiently, but not so low that the organotelluride compound decomposes at relatively low temperatures. If the decomposition temperature is too low then this could present problems with regard to storage and handling of the organotelluride. The organotelluride should be sufficiently volatile that the material can be transported around the equipment in which the CT, CMT, and MT is to be grown. However, if the organotelluride is too volatile then this can cause problems with storage and handling, for example the organotelluride may have to be cooled or maintained under pressure.

The decomposition temperature and volatility of the organotelluride affects the temperature at which MOVPE can be carried out. Preferably this MOVPE growth temperature for CMT should be lower than 370°C. Preferably the MOVPE growth temperature for CT should be lower than 350°C, for MT it should be lower than 370°C. The temperature should be relatively low for these materials for a number of reasons. The use of low temperatures results in lower concentration of Hg vacancies in the CMT material. This results in lower carrier concentrations and reduces the need for annealing to remove such vacancies. Lower temperatures would also reduce diffusion of dopant elements in complex structures leading to more abrupt interfaces.

The first step in the decomposition of organotellurium compounds is thought to be the homolytic cleavage of a Te-C bond. This mechanism means that the generation of undesirable by-products, as a result of reactions involving free radicals, is a

problem for some organotellurium compounds. The telluride should therefore be chosen to minimise such by-products.

A number of factors affect the decomposition temperature, volatility, MOVPE temperature and generation of by-products.

Bulky high molecular weight organo groups often result in a low decomposition temperature for the organotellurium compound. This factor must be weighed against the fact that high molecular weight organotellurium compounds often have a low volatility. The decomposition temperature is also affected by the stability of the free radical resulting from homolytic cleavage. Stabilisation might occur as a result of delocalisation of the free radical across the whole molecule. This would suggest groups such as $\text{CH}_2=\text{CHCH}_2$ or $\text{CH}_2=\text{CHCH}=\text{CHCH}_2$ would be suitable. The presence of dimethylcadmium can also affect the decomposition temperature of the organotellurium compound.

The above illustrates that there are quite a large number of conflicting factors that affect which of the many organotellurium compounds would be suitable. The complexity of this chemical system is illustrated by comparing the properties of diisopropyltelluride, diallyltelluride, and methylallyltelluride.

Diisopropyltelluride is probably the precursor most commonly used for the growth of CT and CMT. The MOVPE growth temperature using the diisopropyl compound and dimethylcadmium is typically 370°C for CMT. It might be thought that diallyltelluride would be an ideal precursor for CMT since it has a similar molecular weight to the diisopropyl compound but should yield a stable free radical. However it turns out that the diallyl tellurium compound is unstable at room temperature, so that storage and handling of this compound is a problem. It might also be thought that the low vapour pressure of diallyltelluride could be compensated by replacing one of the allyl groups with a methyl group. The synthesis of methylallyltellurium is described in GB 2,249,790. Indeed the methylallyltellurium compound does have a

very low decomposition temperature (20% decomposed at 300°C in hydrogen) and is volatile (5.98 Torr at 25°C) but unfortunately the process leads to highly undesirable by-products.

5 As mentioned above, the synthesis of methylallyltellurium is described in GB 2,249,790. The method disclosed in this document is suitable for the synthesis of other organo telluride compounds having mixed organo groups. The method involves the reversible reaction of R_2Te_2 with R'_2Te to give the compound $RR'Te$. A problem associated with this synthesis is that, if the boiling points of $RR'Te$ and
10 R'_2Te are similar then the equilibrium of the reaction can not be driven completely to the $RR'Te$ product by distillation. This means that the product is contaminated with the starting materials.

It is an objective of this invention to provide new methods of fabricating MT, CT,
15 and CMT devices that reduces the above mentioned problems associated with the prior art methods. It is a further objective of the invention to provide a new method of synthesising organoselenium and organotellurium compounds that reduce the above mentioned problems with the prior art methods. It is a yet further objective of the invention to provide a new organotellurium precursor that is suitable for use in
20 the fabrication of CT, MT, and CMT devices and that reduces the above mentioned problems associated with the prior art organotellurium precursors.

According to a first aspect, the invention provides a method of depositing $Hg_{1-x}Cd_xTe$ onto a substrate, in a MOVPE technique, where $0 \leq x \leq 1$; comprising
25 the step of reacting together a volatile organotellurium compound, and one or both of (i) a volatile organocadmium compound and (ii) mercury vapour; characterised in that the organotellurium compound is isopropylallyltelluride.

The method of depositing $Hg_{1-x}Cd_xTe$ can be used to fabricate MT, CT, and CMT
30 electronic devices, such devices including solar cell, infrared emitter, and infrared sensing devices. If $x=0$ then the isopropylallyltelluride is reacted with mercury

vapour in the absence of an organocadmium compound, the MOVPE reaction resulting in mercury telluride. If $x = 1$ then the isopropylallyl compound may be reacted with the organocadmium compound in the absence of mercury vapour, the MOVPE reaction resulting in cadmiumtelluride. The fabrication of CT by this method may also be assisted by the presence of mercury vapour.

This method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ is particularly advantageous because the temperature at which the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ layer or layers are deposited is low. The method enables the efficient deposition of polycrystalline CdTe. The method also alleviates the production of undesirable by-products and promotes the efficient deposition of MT and CMT.

Preferably the organocadmium compound is an alkyl cadmium compound, more preferably the alkyl cadmium compound is dimethyl cadmium.

Advantageously the substrate comprises one of the materials selected from: glass, glass coated with indium tin oxide, CdTe, CdZnTe, GaAs, GaAs/Si, CdTe/GaAs, and Si.

The temperature of the substrate during the MOVPE deposition is, preferably, maintained at a temperature in the range 150°C to 350°C ; more preferably the temperature of the substrate is in the range 250°C to 300°C ; and yet more preferably the substrate temperature is in the range 150°C to 300°C .

According to a second aspect, the invention provides a method of fabricating an electronic device comprising the steps of (a) depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ onto a substrate by the above mentioned method, according to the invention, of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$; and (b) connecting at least two electrodes to the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

The connection of the electrodes may occur as a result of the deposition of $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ onto the electrodes or by the deposition of the electrodes onto the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

- 5 Preferably the method of fabricating a device further comprises the step of doping the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$. Advantageously the method of fabricating a device comprises the step of doping the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ material in such a manner that a p-n junction is formed. In an alternative aspect the method of fabricating a device comprises the step of growing a passivating layer of CdTe on the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

10

According to a third aspect the invention provides a device obtainable by the above mentioned method of making a device. According to a fourth aspect the invention provides $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ or doped $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ obtainable by the above mentioned method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ by MOVPE. According to a fifth aspect, the

- 15 invention provides a new organotellurium compound, namely isopropylallyltelluride.

According to a sixth aspect the invention provides a method for the preparation of a tellurium or selenium compound of the formula RaMRb , where M is selenium or tellurium, and where Ra and Rb are different organic groups each independently
20 selected from C1 to C20 alkyl, alkenyl, or aryl; characterised in that the method comprises the step of reacting the compound RaMA , where A is an alkali metal, with the compound RbX , where X is halogen.

- 25 An advantage of this method is that the RaMRb is produced at relatively high yields and purities.

Advantageously the method comprises the further step of reacting a compound ARa with M, thereby producing RaMA .

- 30 Preferably A is lithium, more preferably X is bromine, yet more preferably M is tellurium.

The invention will now be described, by way of example only, with reference to the following figures:

Figure 1 shows a schematic diagram of an arrangement for fabricating CT, MT, and
5 CMT devices;

Figure 2 shows a typical MT layer grown with isopropylallyltelluride; and

Figures 3a, b, and c show three devices according to the invention.

The starting material for the preparation of isopropylallyltelluride was isopropyl lithium prepared by the method disclosed in EP 525 881 A1. A further method by which the isopropyl lithium compound could be prepared is described in the paper by H Gilman et al in J. Am. Chem. Soc. 1941, volume 63, p 2479. Over a period of 2 hours, a precooled (0°C) solution of 700 cm³ of iPrLi (2.13 moles dm⁻³ in pentane, 1.49 mole) was added dropwise with vigorous stirring to a cooled (0°C)
15 suspension of 191.4g (1.50 mol) of elemental tellurium powder in 1.5 dm³ of THF. On complete addition, the cloudy solution was stirred for a further 1 hour at 20°C.

The iPrTeLi solution was recooled to 0°C and a precooled (0°C) solution of 130 cm³ (1.50 mol) of allyl bromide in 100 cm³ of THF was added dropwise over 1.5
20 hours. The resulting cloudy yellow solution was left to stir at ambient temperature overnight. The bulk of the solvents were removed by distillation under reduced pressure. The final ca. 500 cm³ of volatiles, containing the product, were collected by trap-to-trap distillation *in vacuo*. The pure product, a clear bright yellow liquid, was obtained by careful fractional distillation at low pressure (ca. 0.2 Torr) through
25 a high efficiency (30 theoretical plate) Spaltrohr® distillation column. Overall yield of pure product = 88%.

A schematic diagram of the apparatus, shown in figure 1, is suitable for use in the deposition of a CMT, CT, or MT layer. The apparatus comprises a reaction vessel (1), bubblers (2, 3, and 4) and a number of valves (numbered 5 to 11). Essentially hydrogen is mixed with an organometallic compound or compounds. The mixture of gasses is then flowed over a substrate (12) contained in the reaction vessel (1). The reaction vessel (1) also contains a mercury reservoir (13). Heat is applied to the reaction vessel and to the mercury reservoir as required so that a CMT, MT, or CT layer is deposited upon the substrate (12).

10 Preparation of a CMT layer

CMT is grown by the interdiffused multilayer process (IMP) described in GB 2 146 633 B. The process involves the alternate growth of CT and MT. The CT and MT, which are in the form of very thin layers, are then interdiffused to produce CMT. The CT layers can be deposited even in the presence of mercury vapour so that the alternate layers are fabricated simply by interrupting the supply of the organocadmium compound. When the organocadmium compound is present the CT layer is deposited, when it is absent the MT layer is deposited. The value of x in the $Hg_{1-x}Cd_xTe$ produced by the IMP process is determined by the relative thicknesses of the CT and MT layers.

A bubbler (2) contains dimethylcadmium and a second bubbler (3) contains isopropylallyltelluride. Hydrogen is passed through valve (5) and flows towards the reaction vessel. Hydrogen is also passed through the isopropylallyltelluride bubbler (3) by means of valves (7) and (10) and becomes mixed with the organotelluride compound. The hydrogen/organotelluride mixture is diluted by the hydrogen that has passed through the valve (5) and passes into the reaction vessel (1). Valves 8 and 11 are alternately held open and closed. When valves (8) and (11) are open hydrogen passes through the bubbler (2) and becomes mixed with dimethylcadmium. The dimethylcadmium/hydrogen becomes mixed with the other gasses and flows into the reaction vessel (1).

A mercury reservoir (13) and substrate (12) are placed in the reaction vessel (1). The temperature of the vessel wall in the vicinity of the substrate (12) is maintained at a temperature equal to or greater than the mercury vessel temperature. A water cooling jacket (not shown) at one end of the vessel (1) condenses out the unreacted mercury and prevents overheating of the reaction vessel (1). The exhaust vapour stream (14) is then mixed with a further stream of hydrogen and passed through an activated graphite filter to remove unreacted material and by-products.

The partial pressures of the organometallic compounds are controlled by controlling the flow of hydrogen through the valve (5) and through the bubblers (2) and (3). They are also controlled by controlling the temperatures of the bubblers (2) and (3). The apparatus will typically also comprise by-pass lines (not shown in figure 1) that allow hydrogen to pass through the apparatus while preventing its flow through the bubblers.

The substrate comprises a buffer layer of epitaxial CdTe grown on (100) GaAs or on (100) GaAs mis-oriented, for example 2° towards either (110) or (111)B.

The isopropylalyltelluride partial pressure was 1.7 Torr during the MT part of the cycle and 1.2 Torr for the CT part of the cycle. The Cd:Te ratio for the CT part of the cycle was 1.6. The MOVPE growth temperature was 300°C . In this way a layer thickness of $4.5\ \mu\text{m}$ was obtained after growth of 25 IMP cycles. It proved possible to vary the composition of the CMT ie x by altering the ratio of the CdTe and HgTe IMP times. The precursor ratios given in this section and in the CT and MT preparation section below are based on an estimated vapour pressure of 1.7 Torr at 25°C for the isopropylalyltelluride and on a vapour pressure of 36 Torr at 25°C for dimethylcadmium.

Preparation of a MT and CT Layer

The thicknesses quoted for MT and CT layers described below, were obtained after 20 minutes of growth and were measured by examination of a cleaved edge under a microscope.

The apparatus of figure 1 can also be used to fabricate CT and MT layers. For a CT layer or layers the mercury reservoir remains present in the reaction vessel. It is possible to grow the CT with or without the application of heat to the mercury reservoir (13). For an MT layer the flow of hydrogen through the bubbler containing the dimethylcadmium is prevented, so that no dimethylcadmium is present in the reaction vessel. The substrate and buffer layer used also remain unchanged.

For the preparation of MT the gas stream in the reaction vessel either had the same composition as that which left the isopropylallyltelluride bubbler or was slightly diluted by passing hydrogen through the valve (5). The growth rate for MT was found to be around 10 μm per hour at MOVPE growth temperatures of 290 to 325°C. An image of the surface of a typical MT layer grown with isopropylallyltelluride is shown in figure 2.

For the deposition of CT the Me_2Cd : isopropylallyltelluride ratio was varied between 0.26 and 2.7 by varying the Me_2Cd partial pressure between 0.35 and 2.92 Torr. (It should be noted that the 0.26 ratio resulted in no CT being deposited). The partial pressure of the isopropylallyltelluride was held at approximately 1.3 Torr. In this way 2.5 μm thick films of epitaxial CT were grown on top of the conventionally grown CT buffer layer. The MOVPE growth temperature, at which the 2.5 μm thick film was grown, was 325°C and the ratio of dimethylcadmium to isopropylallyltelluride was 1.6.

Keeping the temperature at 325°C and increasing the Cd:Te ratio to 2.7 resulted in layers of CT that were very dark grey in colour with an iridescent hue. Examination

under the microscope revealed them to consist mainly of coalesced bumps on top of some shinier material. It was concluded that the coalesced bumps were $7\mu\text{m}$ of polycrystalline CdTe. The ability to deposit polycrystalline CdTe efficiently at 300°C , perhaps onto glass substrates, may have applications for solar cells.

5

Dopants

The layer of CMT, MT, or CT grown on the substrate may include one or more dopants. The dopant can be introduced using the apparatus of figure 1. The organic compound of the dopant can be held in a bubbler (4) as shown in figure 1. The flow of the dopant into the reaction vessel (1) can be controlled by opening or closing the valves (6) and (7). With valves (6) and (7) open hydrogen is bubbled through the bubbler (4) and is mixed with the dopant compound. Alternatively a volatile hydride of the dopant in hydrogen may be used.

15

Examples of dopants and their hydrides are as follows: Si, Ge, As, and P from their respective hydrides: SiH_4 , GeH_4 , AsH_3 , and PH_3 . A supply of hydrides eg SiH_4 may be supplied direct from gas cylinders. The hydrides may optionally be diluted in hydrogen.

20

Examples of organic compounds of the dopants are as follows: Al, Ga, As, P, and I from the respective alkyls: $(\text{CH}_3)_3\text{Al}$, $(\text{CH}_3)_3\text{Ga}$, $(\text{CH}_3)_3\text{As}$, $(\text{CH}_3)_3\text{P}$, $\text{C}_2\text{H}_5\text{I}$, and $\text{C}_4\text{H}_9\text{I}$. A further good source of As is $\text{As}(\text{NMe})_3$.

25 Devices

Figures 3 shows three electronic devices according to the invention. Figure 3a shows a layer of semiconductor material (2) connected to two electrodes (1). The layer (2) may comprise CT, CMT, or MT and may be either n-type, p-type, or undoped. The device, shown in figure 3a, may form part of an infrared detector.

30

Such detectors operate by monitoring the change in conductivity of the layer (2) that occurs when the layer is exposed to infrared radiation.

Figures 3b and 3c show electronic devices that have one or more n-type regions (4), one or more p-type regions (3), and one or more electrodes (1) connected to the n-type and p-type regions. The n-type and p-type regions may be fabricated from CT, CMT, or MT. The devices of figures 3b and 3c operate by generating a potential difference between the n-type region or regions and the p-type region or regions (3) when the devices are illuminated with electromagnetic radiation. The potential difference can be used to detect the radiation or it can be used as a source of electric power.

Claims

1. Isopropylallyltelluride.
 2. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ onto a substrate, in a MOVPE technique, where $0 \leq x \leq 1$; comprising the step of reacting together a volatile organotellurium compound, and one or both of (i) a volatile organocadmium compound and (ii) mercury vapour; characterised in that the organotellurium compound is isopropylallyltelluride.
 3. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 2 wherein the organocadmium compound is an alkyl cadmium compound.
 4. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 3 wherein the alkyl cadmium compound is dimethyl cadmium.
 5. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 2 wherein $0 < x < 1$.
 6. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 2 wherein $x=0$.
 7. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 2 wherein $x=1$.
 8. A method according to Claim 7 wherein the reaction is carried out in the presence of mercury vapour.
 9. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 2 wherein the substrate comprises glass, or glass coated with indium tin oxide, or CdTe, or CdZnTe, or GaAs, or GaAs/Si, or CdTe/GaAs, or Si.
-
-

10. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 2 wherein the temperature of the substrate is maintained at a temperature in the range 150°C to 350°C.

11. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 10 wherein the temperature of the substrate is maintained at a temperature in the range 150°C to 300°C.

12. A method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ according to Claim 11 wherein the temperature of the substrate is maintained at a temperature in the range 250°C to 300°C.

13. A method of fabricating an electronic device comprising the steps of (a) depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ onto a substrate by a method according to any one of Claims 2 to 12; and (b) connecting at least two electrodes to the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

14. A method of fabricating an electronic device according to Claim 13 wherein the method further comprises the step of doping the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

15. A method of fabricating an electronic device according to Claim 13 wherein method comprises the further step of doping the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ material in such a manner that a p-n junction is formed.

16. A method of fabricating an device according to one of Claims 13 or 14 wherein the method further comprises the step of growing a passivating layer of CdTe on the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

17 A device obtainable by a method according to one of Claims 13 to 16.

18. An infrared detector comprising an array of devices, each device being obtainable by a method according to one of Claims 13 to 16.

19. $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ obtainable by a method according to one of Claims 2 to 12.

20. A method for the preparation of a tellurium or selenium compound of the formula RaMRb , where M is selenium or tellurium, and where Ra and Rb are different organic groups each independently selected from C1 to C20 alkyl, alkenyl, or aryl; characterised in that the method comprises the step of reacting the compound RaMA , where A is an alkali metal, with the compound RbX , where X is halogen.

21. A method according to Claim 20 wherein the method comprises the further step of reacting a compound ARa with M, thereby producing RaMA .

22. A method according to Claim 20 or Claim 21 where A is lithium.

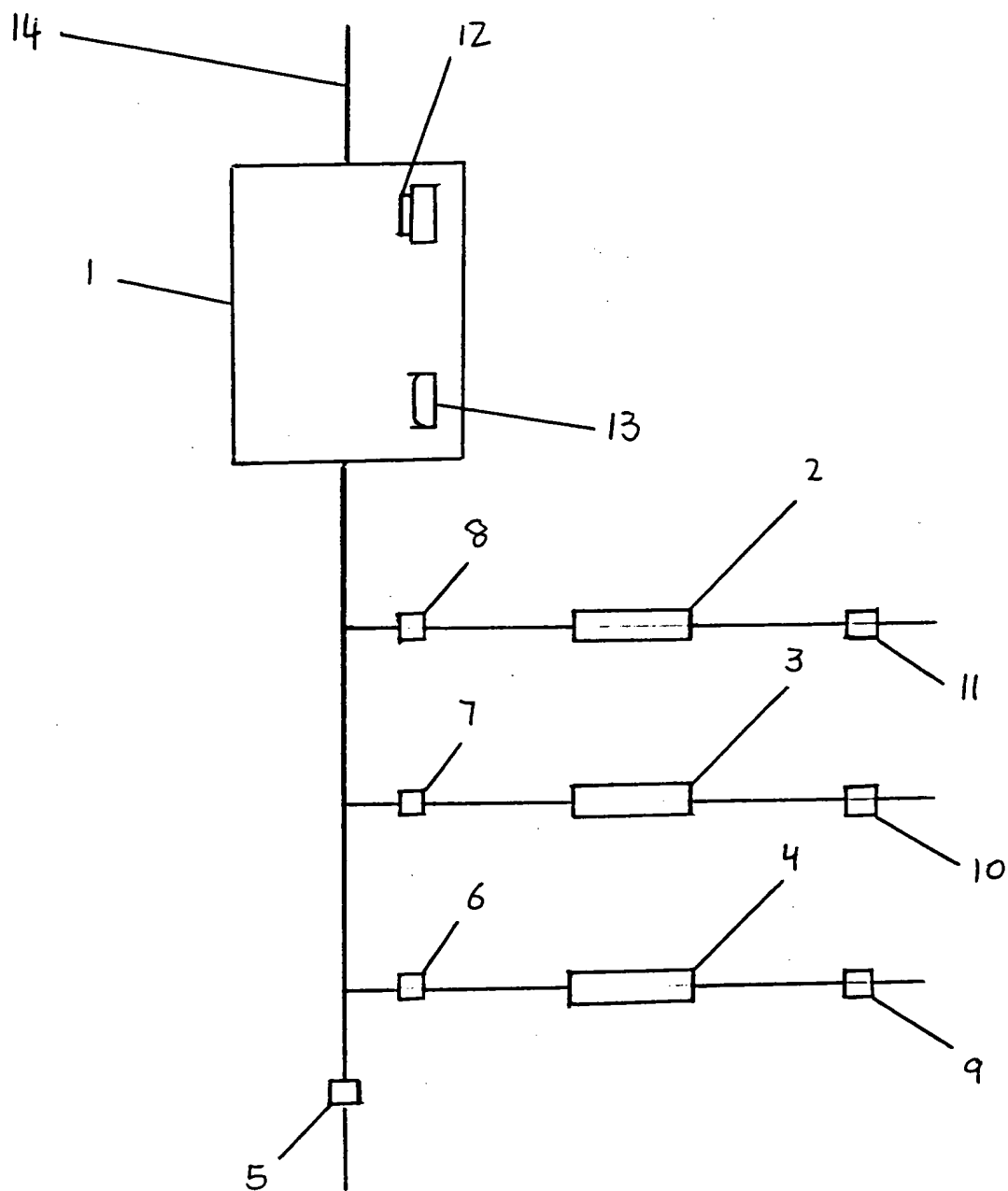
23. A method according to one of Claims 20 to 22 where X is bromine.

24. A method according to one of Claims 20 to 23 where M is tellurium.

Abstract

The invention relates to a method of depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ onto a substrate, in a MOVPE technique, where $0 \leq x \leq 1$; comprising the step of reacting together a volatile organotellurium compound, and one or both of (i) a volatile organocadmium compound and (ii) mercury vapour; characterised in that the organotellurium compound is isopropylallyltelluride. The invention also relates to a new organotellurium compound, namely isopropylallyltelluride and to devices, such as infrared sensors and solar cells, that comprise $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ materials.

Fig. 1





2/3

Fig. 2





Fig. 3a

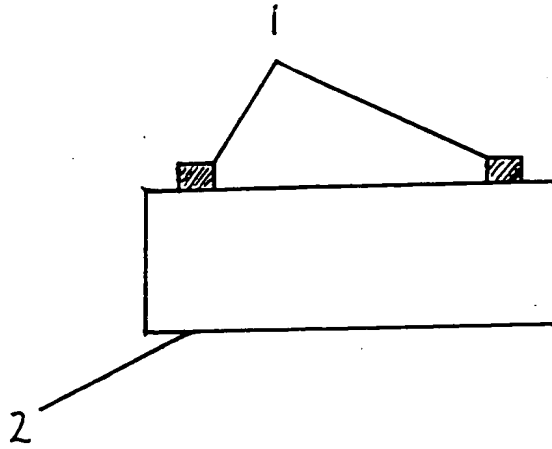


Fig. 3b

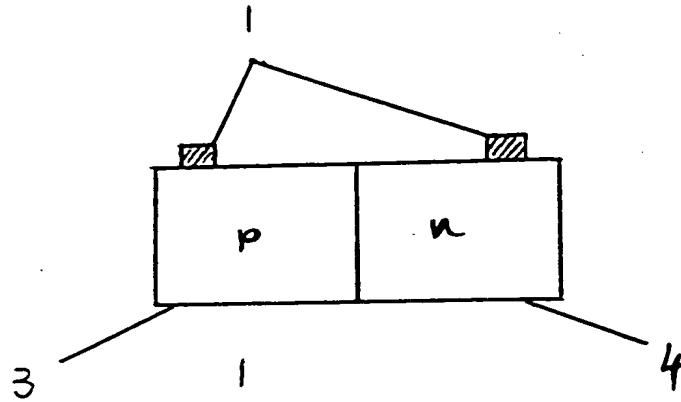
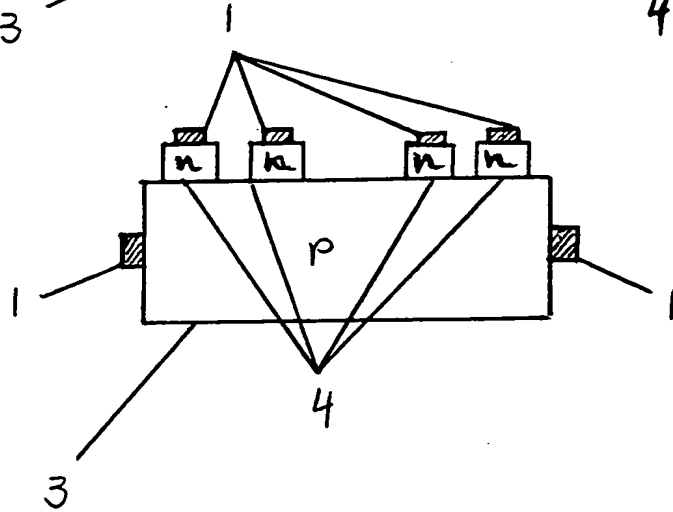


Fig. 3c



PCT/64300'032UA

2218100

DERF